

L Number	Hits	Search Text	DB	Time stamp
-	71	356/\$.ccls. and (gate adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/02 14:04
-	59	356/\$.ccls. and (gate adj oxide)	USPAT	2003/07/02 14:05
-	5	(gate adj oxide) and thickness and (high\$1k) and scatter\$	USPAT	2003/07/02 15:19
-	55	356/\$.ccls. and (gate adj oxide) and thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/02 15:25
-	231	(hallyal-arvind singh-bhanwar subramanian-ramkumar).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/02 15:26
-	18	(hallyal-arvind singh-bhanwar subramanian-ramkumar).in. and (gate adj oxide) and thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/02 15:26
-	22	356/\$.ccls. and (gate adj oxide) and (thickness or uniform\$) and scatter\$	USPAT	2003/07/08 14:44
-	28	356/\$.ccls. and (gate adj oxide) and (thickness or uniform\$) and scatter\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/08 16:56
-	9	("4710030" "4750822" "5298970" "5608526" "5798837" "5978074" "6060374" "6081330" "6381009").PN.	USPAT	2003/07/08 16:28
-	5	("4710030" "4750822" "5298970" "5608526" "5798837" "5978074" "6060374" "6081330" "6381009").PN. and scatter\$	USPAT	2003/07/08 16:29
-	0	("4710030" "4750822" "5298970" "5608526" "5798837" "5978074" "6060374" "6081330" "6381009").PN. and scatter\$ and (gate adj oxide)	USPAT	2003/07/08 16:29
-	32	250/\$.ccls. and (gate adj oxide) and (thickness or uniform\$) and scatter\$	USPAT	2003/07/08 16:30
-	30	250/\$.ccls. and (gate adj oxide) and (thickness or uniform\$) and scatter\$ not 356/\$.ccls.	USPAT	2003/07/08 16:30
-	33	250/\$.ccls. and (gate adj oxide) and (thickness or uniform\$) and scatter\$ not 356/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/08 16:45
-	622	((gate adj oxide) with (thickness or uniform\$)) and scatter\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 12:10
-	19	((gate adj oxide) with (thickness or uniform\$)) and scatter\$.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/08 16:46
-	2	356/630-632.cccls. and (gate adj oxide) and scatter\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 16:26
-	14	((gate adj oxide) with (thickness or uniform\$)).ab. and scatter\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 12:38

-	0	("5862054" "6060374" "5880040").pn. and scatter\$	USPAT	2003/07/09 12:37
-	3	("5862054" "6060374" "5880040").pn.	USPAT	2003/07/09 15:11
-	9452	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. ((gate adj oxide) with (thickness or uniform\$)) and scatter\$ and (nitrid\$ or nitrogen\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 12:41
-	9035	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. ((gate adj oxide) with (thickness or uniform\$)) and scatter\$.ab. and (nitrid\$ or nitrogen\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 12:41
-	4	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and ((gate adj oxide) with (thickness or uniform\$)) and scatter\$.ab. and (nitrid\$ or nitrogen\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 12:44
-	1	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and ((gate adj oxide) with (thickness or uniform\$)).ab. and scatter\$ and (nitrid\$ or nitrogen\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 12:45
-	31	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and ((gate adj oxide) with (thickness or uniform\$)) and scatter\$ and (nitrid\$ or nitrogen\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/10 15:43
-	3	("6528433" "5904523" "6060374").pn.	USPAT	2003/07/09 15:12
-	2	("20020023900" "20030042432").pn.	US-PGPUB	2003/07/09 15:13
-	116	356/630-632.cccls. and (semiconductor or wafer) and scatter\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 16:26
-	10	356/630-632.cccls. and (semiconductor or wafer) and scatter\$.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/10 11:43
-	1	356/630-632.cccls. and (semiconductor or wafer) and (scatterometry with thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 16:36
-	0	(scatterometry with nitrogen) and (semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 16:36
-	0	(scatterometry with nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 16:36
-	679	(scatter\$ with nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 16:36
-	195	(scatter\$ with nitrogen) and (semiconductor or wafer or (gate adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 16:37
-	55	(scatter\$ with nitrogen) and (semiconductor or wafer or (gate adj oxide)) and scatter\$.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/09 16:39

	47	(scatter\$ with nitrogen) and (semiconductor or wafer or (gate adj oxide)) and scatter\$.ab. not (electron near4 beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/07/09 16:40
	26	(scatter\$ with nitrogen) and (semiconductor or wafer or (gate adj oxide)) and (scatter\$ and (nitrogen or nitride\$)).ab. not (electron near4 beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/07/09 16:40
	9	("5867276" "5877880" "5880838" "6051348" "6081334" "6141107" "6245584" "6383888" "6423977").PN.	USPAT	2003/07/10 11:16
	1	("5867276" "5877880" "5880838" "6051348" "6081334" "6141107" "6245584" "6383888" "6423977").PN. and scatter\$.ab.	USPAT	2003/07/10 11:18
	4	("4710642" "5164790" "5241369" "5703692").PN.	USPAT	2003/07/10 11:17
	4	("5867276" "5877880" "5880838" "6051348" "6081334" "6141107" "6245584" "6383888" "6423977").PN. and scatteromets\$	USPAT	2003/07/10 11:18
	17	356/630-632.ccls. and (semiconductor or wafer) and scatterom\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/07/10 12:01
	16	356/630-632.ccls. and (semiconductor or wafer) and scatterom\$ not scatter\$.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/07/10 11:43
	6	356/237.4,237.5.ccls. and (semiconductor or wafer) and scatterom\$ and thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/07/10 14:17
	7	250/559.27.ccls. and (semiconductor or wafer) and scatterom\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/07/10 11:55
	1	250/559.27.ccls. and (semiconductor or wafer) and scatterom\$	USPAT; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/07/10 11:55
	21	356/630-632.ccls. and scatterom\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/07/10 12:01
	10	356/630-632.ccls. and scatterom\$	USPAT	2003/07/10 12:01
	154	356/630-632.ccls. and scatter\$	USPAT	2003/07/10 12:01
	20	356/630-632.ccls. and scatter\$.ab.	USPAT	2003/07/10 12:02
	20	356/630-632.ccls. and scatter\$.ab. and scatter\$	USPAT	2003/07/10 12:02
	35	356/\$.ccls. and (semiconductor or wafer) and scatterom\$.ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/07/10 14:17
	8	("5393624" "5867276" "5923423" "6100985" "6259521" "6266125" "6388253" "6424417").PN.	USPAT	2003/07/10 15:27
	2	("5393624" "5867276" "5923423" "6100985" "6259521" "6266125" "6388253" "6424417").PN. and (nitrogen\$ or nitride\$)	USPAT	2003/07/10 15:27

-	61	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and ((gate adj oxide) with cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/10 15:54
-	19	(438/263,786,514,14-18,769 257/e21.193,e29.162 700/121,108,109 702/181).ccls. and (gate adj oxide).ab. and ((gate adj oxide) with cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/10 15:57